

**M5456WP**

7-UNIT 400mA DARLINGTON TRANSISTOR ARRAY

**DESCRIPTION**

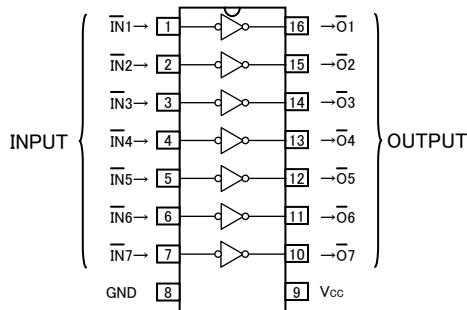
M5456WP are seven-circuit collector-current synchronized Darlington transistor arrays. The circuits are made of PNP and NPN transistors. Both the semiconductor integrated circuits perform high-current driving with extremely low input-current supply.

**FEATURES**

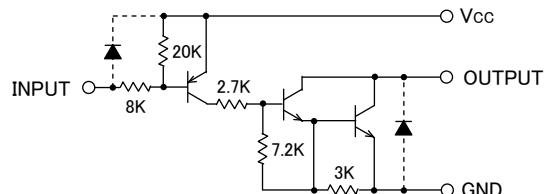
- High breakdown voltage ( $BVCEO \geq 50V$ )
- High-current driving ( $Ic(max) = 400mA$ )
- Active L-level input

**APPLICATION**

Interfaces between microcomputers and high-voltage, high-current drive systems, drives of relays and printers, and MOS-bipolar logic IC interfaces

**PIN CONFIGURATION**

Package type 16P4X

**CIRCUIT DIAGRAM**

The seven circuits share the VCC and GND.

The diode, indicated with a dotted line, is parasitic, and cannot be used.  
Unit: Ω

**FUNCTION**

The M5456 is produced by adding PNP transistors to M54522 inputs. Seven circuits having active L-level inputs are provided.

Resistance of  $8k\Omega$  is provided between each input and PNP transistor base. The input emitters are connected to Vcc pin (pin 9). Output transistor emitters are all connected to the GND pin (pin 8).

Collector current is 400mA maximum. Collector-emitter supply voltage is 50V maximum.

These ICs are optimal for drivers that are driven with N-MOS IC output and absorb collector current.

**ABSOLUTE MAXIMUM RATINGS (Unless otherwise noted,  $T_a = -20 \sim +75^\circ C$ )**

Symbol	Parameter	Conditions	Ratings	Unit
Vcc	Supply voltage		10	V
VCEO	Collector-emitter voltage	Output, H	-0.5 ~ +50	V
Ic	Collector current	Current per circuit output, L	400	mA
VI	Input voltage		-0.5 ~ Vcc	V
Pd	Power dissipation	$T_a = 25^\circ C$ , when mounted on board	1.47	W
T <sub>opr</sub>	Operating temperature		-20 ~ +75	°C
T <sub>stg</sub>	Storage temperature		-55 ~ +125	°C

MITSUBISHI SEMICONDUCTOR <TRANSISTOR ARRAY>

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**RECOMMENDED OPERATING CONDITIONS**

Symbol	Parameter	Limits			Unit
		min	typ	max	
Vcc	Supply voltage	4	5	8	V
Vo	Output voltage	0	—	50	V
Ic	Collector current (Current per 1 circuit when 7 circuits are coming on simultaneously)	Vcc=5V Duty Cycle no more than 10%	0	—	350
		Vcc=5V Duty Cycle no more than 30%	0	—	200
ViH	"H" input voltage	Vcc-0.2	—	Vcc	V
ViL	"L" input voltage	0	—	Vcc-3	V

**ELECTRICAL CHARACTERISTICS (Unless otherwise noted, Ta = -20 ~ +75°C)**

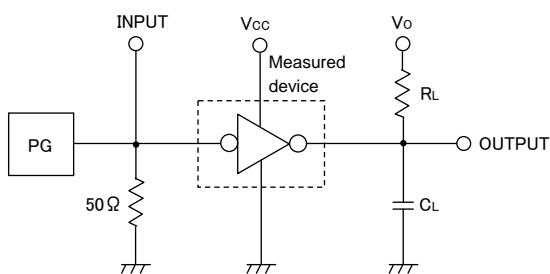
Symbol	Parameter	Test conditions	Limits			Unit
			min	typ *	max	
V(BR)CEO	Collector-emitter breakdown voltage	ICEO = 100 μA	50	—	—	V
VCE(sat)	Collector-emitter saturation voltage	VI = Vcc - 3V, IC = 350mA	—	1.1	2.2	V
		VI = Vcc - 3V, IC = 200mA	—	0.9	1.6	
II	Input current	VI = Vcc - 3.5V	—	-0.3	-0.58	mA
Icc	Supply current (one circuit coming on)	Vcc=5V, VI=Vcc-3.5V	—	1.4	3.0	mA
hFE	DC amplification factor	VCE = 4V, Vcc=5V, IC = 350mA, TA = 25°C	2000	10000	—	—

\* : The typical values are those measured under ambient temperature (Ta) of 25°C. There is no guarantee that these values are obtained under any conditions.

**SWITCHING CHARACTERISTICS (Unless otherwise noted, Ta = 25°C)**

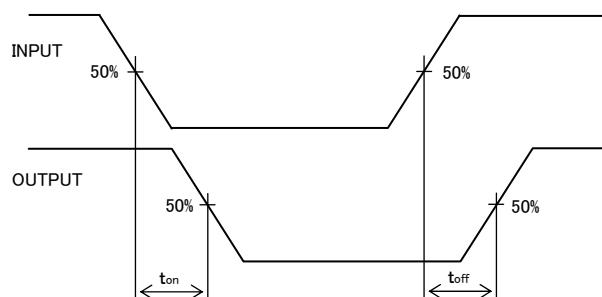
Symbol	Parameter	Test conditions	Limits			Unit
			min	typ	max	
t <sub>on</sub>	Turn-on time	C <sub>L</sub> = 15pF (note 1)	—	95	—	ns
t <sub>off</sub>	Turn-off time		—	2500	—	ns

**NOTE 1 TEST CIRCUIT**



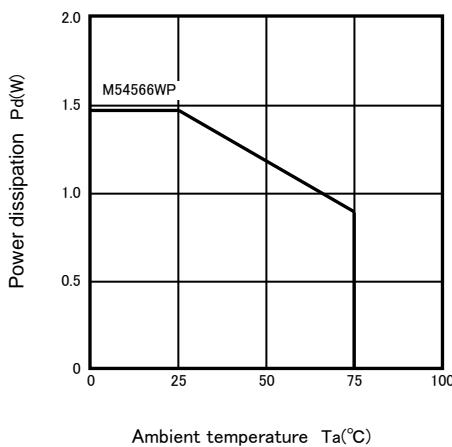
- (1) Pulse generator (PG) characteristics: PRR = 1kHz, tw = 10μs, tr = 6ns, tf = 6ns, ZO = 50Ω, VI = 1 to 4V
- (2) Input-output conditions : RL = 30Ω, VO = 10V, VCC = 4V
- (3) Electrostatic capacity CL includes floating capacitance at connections and input capacitance at probes

**TIMING DIAGRAM**

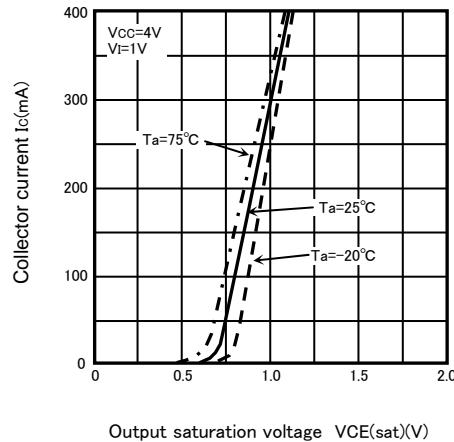


## TYPICAL CHARACTERISTICS

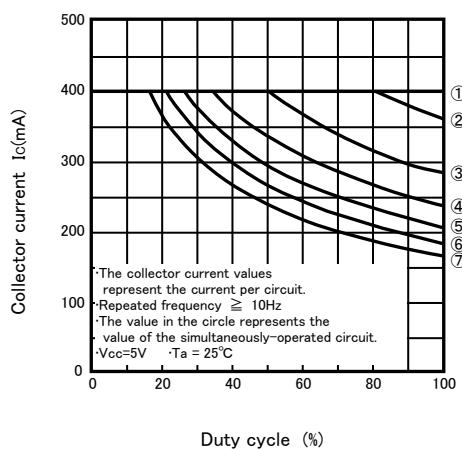
Thermal Derating Factor Characteristics



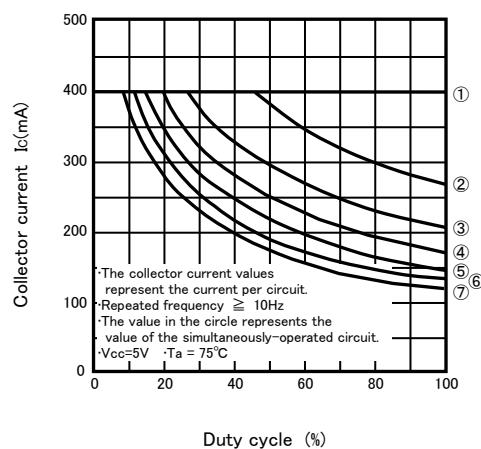
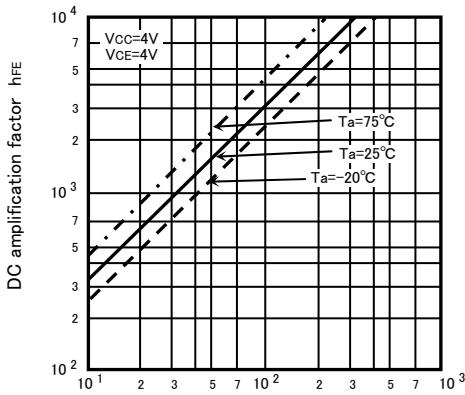
Output Saturation Voltage



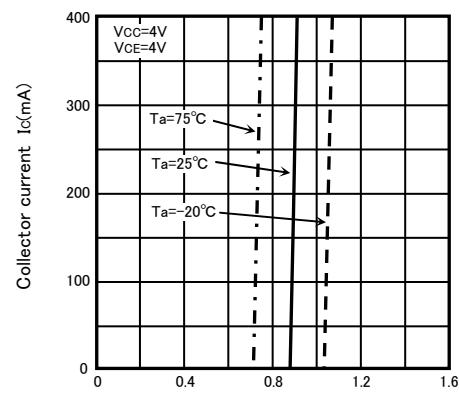
Duty-Cycle-Collector Characteristics



Duty-Cycle-Collector Characteristics

DC Amplification Factor  
Collector Current Characteristics

Grounded Emitter Transfer Characteristics



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